

AllnGaP LED DICE

Part NO.: AOC-112RxB Series

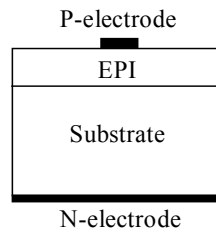
Features

- Red Color Emission
- Excellent performance and high efficiency
- Great reliability even in harsh environment

Description

AOC-112RxB series is a red color emitting AllnGaP LED grown by MOCVD technique. Its structure enables enhanced quantum efficiency and therefore a greater light intensity. This device is designed to suit the growing demand in the compact size electronic goods.

Chip Dimensions



Chip Size : 10.8mil×10.8mil±0.5mil

Bonding Pad : φ4.0mil±0.4mil

Chip Thickness : 6.5mil±1.0mil

Specification and Optical Characteristics

Measuring Item	Symbol	Condition	Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F=20mA$	1.70	-	2.20	V
Reverse Current	I_R	$V_R=-5V$	-	-	1.0	μA
Dominant Wavelength	λ_d	$I_F=20mA$	616	-	645	nm
Max. Junction Temperature	T_{max}	-	≤ 115			$^{\circ}C$
Max. DC forward current	I_F	$T_a = 25^{\circ}C$	≤ 50			mA
Max. pulse forward current (Pulse width 0.1 msec, frequency=1 kHz.)	I_{fm}	$T_a = 25^{\circ}C$	≤ 100			mA
Storage temperature	T_{stg}	Chip on tape	0 ~ 40			$^{\circ}C$
		Only chip	-40 ~ 80			

Available Dominate Wavelength and Iv Matrix

Part No.	Wavelength Range	≥ 30 mcd	≥ 40 mcd	≥ 50 mcd	≥ 60 mcd	≥ 70 mcd	≥ 80 mcd	≥ 90 mcd	≥ 100 mcd	≥ 110 mcd
112 RSB	616 ~ 625 nm	-	-	-	-	-	-	-	-	-
112 RMB	620 ~ 630 nm	-	C	D	E	F	G	H	-	-
112 RLB	625 ~ 635 nm	B	C	D	E	F	-	-	-	-

Not:

1. All measurements are done with AOC's standard testing equipment.
2. Luminance intensity is measured on bare chip.
3. Above contents are subject to change without notice.
4. Special requests are also welcome, please contact AOC's sale representative for any request.